

2018

# **The Belle II Silicon Vertex detectors**

Daniel Pitzl, DESY London, 7.11.2023

2023



- SuperKEKB
- Belle II
- Vertex detectors:
  - ► SVD
  - ► PXD
- performance
- coming years

#### **SuperKEKB**



- 7 on 4 GeV: 10.58 GeV
  - 83 mrad crossing angle
  - ▶ 0.3 mm length of luminous region
  - vertical focusing β\* down to 0.6 mm (ultimately 0.3 mm)
- beam currents up to 3 A in 2500 bunches
  - 4 ns bunch spacing
  - ▶ 250 MHz crossing rate (6× LHC)
  - continuous top-up injection
  - "early phase 3": 2019-2022
    - ► L<sub>peak</sub> 4.7 10<sup>34</sup>/cm<sup>2</sup>s, L = 427 fb<sup>-1</sup>

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# **Belle II**



- partial upgrade from Belle:
  - new particle ID (TOP and ARICH)
  - new drift chamber (axial and stereo, He-ethane)
  - new silicon vertex (strips and pixels)
  - new smaller Be beam pipe
  - final focus magnets in the detector volume
- up to 30 kHz trigger rate
  - 4 ns bunch spacing not fully resolved
- 2020-22 operated under strict Covid-19 protocol:
  - no foreign travel
  - PXD had one postdoc at KEK
  - remote operation and monitoring

## **Belle II silicon vertex detectors**



diamond radiation sensors



- six layers of silicon sensors:
  - 4 strip layers (SVD, slanted forward sensors)
  - 2 pixel layers (PXD)
  - covering polar angles from 17° to 150° (like the drift chamber)
- double-walled Be beam pipe (with paraffin cooling)
  - inner radius 10 mm

~25 µm transverse vertex resolution (70 fs)

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#### **SVD Ladder**



- Ladder: 2 to 5 Double-Sided Si strip sensors along *z* 
  - AC coupling: block leakage current and bias potential
  - intermediate floating strips improve resolution
  - readout and power distribution on flexible Kapton prints

	Small sensors	Large sensors	Trapezoidal sensors
Readout strips P-side	768	768	768
Readout strips N-side	768	512	512
Readout pitch P-side	$50 \ \mu m$	$75 \ \mu m$	$50 - 75 \ \mu m$
Readout pitch N-side	160 μm	$240 \ \mu m$	$240 \ \mu m$
	L3	L4-6	L4-6



AC-coupled strips on N-type substrate Full depletion voltage: 20-60V Operation voltage: 100V

## readout on flexible Kapton prints



- APV25 (0.25 µm radiation hard IBM CMOS designed at IC and RAL for CMS)
  - thinned to 100 μm, wire bonded to Kapton flex print (fan-in, power, readout)
  - 128 channels: 4 APV for *z*-readout (512 short strips), 6 for rφ (768 long strips)
  - 4 W per module: CO2 cooling pipe attached on top of APVs (not shown)

#### SVD status 2023

- after 4 years of operation:
  - no dead chip (in 1748)
  - very few dead channels (in 224k)
  - efficiency always and everywhere above 98.5%
  - leakage currents as expected from ionizing dose
  - (capacitive) noise increase already saturated:





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## **SVD cluster position resolution**



Ζ

# **SVD timing**



- APV: 50 ns rise time
  - 32 MHz sampling
  - reading 6 or 3 samples



- SVD hit timing:
  - 2.5 ns resolution (p-side: 20 ns drift)
  - cluster time 'grouping' for background rejection

## **SVD space points and ghosts**



- double sided silicon strips: measure z and  $\phi$  projections
  - ▶ space points: all *z*- $\phi$  combinations per module: ghosts
- options: exploit charge and time correlations

#### **Pixel detector**



SVD L5 SVD L4 SVD L3 - PXD L2 (2 of 12 ladders) - PXD L1 (8 ladders)

SVD L3

SVD L4

# **DEPFET pixel**

- monolithic pixel detector: depleted FET
- ionized charge collected by drift at an internal gate (small deep implant)
- DEPFET is off for 19.9/20 μs: gate at +5V
- "readout": modulated drain current: gate at -2V
- **reset** after readout: **Clear** at +15V (punch through)



<sup>-60</sup>V bias (top surface punch through)



pixel size: 50 µm (trans) 55-85 µm (long) 192k pixels

all-silicon module thickness: 75 μm (active) 450 μm (rim) 0.21% X₀

8 W in readout region 2-phase CO<sub>2</sub>



# **Pixel module**

operated in continuous rolling shutter readout mode sensitive for 19.9/20.0 μs 0.5 W in active region: N2 flow cooling

Switcher: 5V gate, 15V clear, 10 MHz (180 nm AMS/IBM HVCMOS) sensor provides power and readout lines

flip chip bump bonding to sensor

Drain Current Digitizer: analog common mode, 256 ADCs (8 bit) (160 nm UMC)

Data Handling Processor: pedestal, zero suppression(65 nm TSMC)trigger, LVDS output

mounting on cooling block: long hole for thermal contraction

#### **Pixel module**



# **DEPFET signal, ADC noise**

- most probable cluster signal:
  - ► 45-70 ADC units
- ADC noise:
  - 0.7 ADU rising to 1.4 with dose
- online threshold:
  - pixel signal > 7 ADU
- (most probable > 3× threshold is enough for > 98% efficiency)



**Total Dose** 

# **PXD L1 efficiency map**

in the 4<sup>th</sup> year of operation (May 2022)



# pixel position resolution

- overlap residuals: 2 hits in the same layers
- MAD = Mean Absolute Deviation (for Gaussian: MAD = 0.8 RMS)
- long clusters: limited head tail algorithm





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# alignment

- tracker alignment uses MillePede II algorithm
  - 6 rigid body parameters per Si sensor
  - 12 deformation parameters (4<sup>th</sup> order 2D Legendre polynomials) per sensor
  - total 3726 parameters (plus 57'680 for drift chamber wires)
- using collision data and cosmics: reaching micron precision
- hierarchical alignment:
  - half-shells
  - ladders
- updated every few days
  - thermal effects

T. Bilka et al. EPJ Web of Conferences 251, 03028 (2021) https://doi.org/10.1051/epjconf/202125103028D. Pitzl (DESY): The Belle II silicon vertex detectors



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 di-muons: compare upper and lower track

# continuous injection





- beam currents reached 1400 mA (half the design)
  - short lifetime (Touchek scattering, synchrotron radiation, residual pressure, scattering losses)
- permanent injection: up to 25 Hz per ring:
  - single or double bunch top-up
  - injected bunch creates background spikes
  - every 10 µs for a few ms
  - detectors stay active during injection
  - first 0.5 ms masked out in trigger (deadtime)
  - pixel detector always integrates over 2 turns: observe damping oscillations

### **PXD event display**



- data event
  - zoomed-in
- 2.6% pixel occupancy
- 50×55 µm pixels
- SVD-PXD matching at the purity limit

#### **2023: PXD completion**



# 2018: lack of quality ladders (in-house production)



# 2023: 40 (all new) modules, same design (same in-house production)

#### **VXD 2023**



• SVD and fully-equipped PXD mounted around modified beam pipe (Au coating, cooling)

# background prediction for the next years

- prediction for 2.8 10<sup>35</sup>/cm<sup>2</sup>s
  - (steady state, without injection backgound)
  - simulation
- LER = 4 GeV positrons
- LER beam gas
- LER Touschek
  - in-bunch Coulomb
- Luminosity collisions



A. Natochii et al. https://arxiv.org/abs/2302.01566

# **PXD L1 occupancy**



- PXD L1 occupancy
  - in the "steady state" (20 ms after the last injection)
  - various running conditions
    2021-2022
- extrapolated
- performance limits:
  - readout buffer size at 3%
  - SVD-PXD track matching at 3% (will improve with intermediate 2<sup>nd</sup> PXD layer)
- large uncharted territory
  - with some safety margin

# and beyond?

- pixels: high granularity
  - long integration without time stamps
  - cluster merging, matching purity



• strips: fast readout

ghosts

measures projections per sensor



- want the best of both technologies:
  - a fast pixel detector
  - see upgrade talk by C. Finck tomorrow







- TheBelle II silicon vertex detectors (strips and pixels) have operated successfully at SuperKEKB since 2019
  - in terms of efficiency, purity, and resolution
  - satisfying the design parameters for the Belle II physics program
- The completed 2-layer pixel detector with all-new modules is expected to provide efficient vertexing for the coming years, with safety margin for occupancy variations







#### impact parameter resolution: Belle II MC vs Belle



#### **SVD ladder components**



#### **0.7%** X<sub>0</sub> per layer (in the active volume)

# material imaging



#### **3-track vertices from nuclear interactions**